

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all previous listings of claims for this application.

1. **(Currently amended)** An apparatus for processing a substrate comprising a frontside and a backside used in the fabrication of an integrated device, the apparatus comprising a reaction chamber, a first load platform, and a second load platform, wherein:

the first load platform and the second load platform are disposed within the reaction chamber;

the first load platform is configured to support a substrate substantially only at the edges thereof, thereby permitting ~~permit~~ a process gas to contact both the frontside and backside of a substrate loaded on the first load platform;

each of the first and second load platforms is dimensioned and configured to directly support the substrate;

the first load platform is mounted outside of the second load platform; and

the first load platform is fixed relative to the second load platform.

2. **(Original)** The apparatus of claim 1, wherein the first load platform is higher than the second load platform.

3. **(Original)** The apparatus of claim 2, wherein the first load platform is substantially directly above the second load platform.

4. **(Original)** The apparatus of claim 2, wherein the first load platform is at least about 10 mm higher than the second load platform.

5. **(Original)** The apparatus of claim 1, wherein the first load platform comprises a plurality of support pins.

6. **(Original)** The apparatus of claim 5, wherein the first load platform comprises three support pins.

7. **(Original)** The apparatus of claim 5, wherein the support pins are made from a material selected from the group consisting of quartz, silicon carbide, and silicon-carbide-coated graphite.

8. **(Original)** The apparatus of claim 1, wherein the second load platform is a susceptor.

9. **(Original)** The apparatus of claim 8, further comprising a heat source.

10. (Original) The apparatus of claim 8, wherein the reaction chamber is configured to deposit epitaxial silicon on a substrate loaded on the second load platform.

11. (Original) The apparatus of claim 1, further comprising a heat source.

12–37. (Canceled)

38. (**Currently amended**) An apparatus for processing a substrate comprising a frontside and a backside used in the fabrication of an integrated device, the apparatus comprising:

a reaction chamber;

a first means for directly supporting the substrate during processing; and

a second means for directly supporting the substrate during processing,

wherein neither the first means for directly supporting the substrate nor the second means for directly supporting the substrate comprises lift pins.

39. (Previously presented) The apparatus of claim 38, wherein the first means of supporting the substrate during processing comprises at least one movable element.

40. (Previously presented) The apparatus of claim 38, wherein the first means of supporting the substrate during processing comprises a support ring.

41. (Previously presented) The apparatus of claim 38, wherein at least a portion of the first means of supporting the substrate during processing is mounted to a slip ring.

42. (Previously presented) The apparatus of claim 41, wherein at least a portion of the first means of supporting the substrate during processing is movable.

43. (Previously presented) The apparatus of claim 38, wherein the second means of supporting the substrate during processing comprises a susceptor.